

# Comparative Spectroscopic Study of Aluminum Nitride Grown by MOCVD in H<sub>2</sub> and N<sub>2</sub> Reaction Environment

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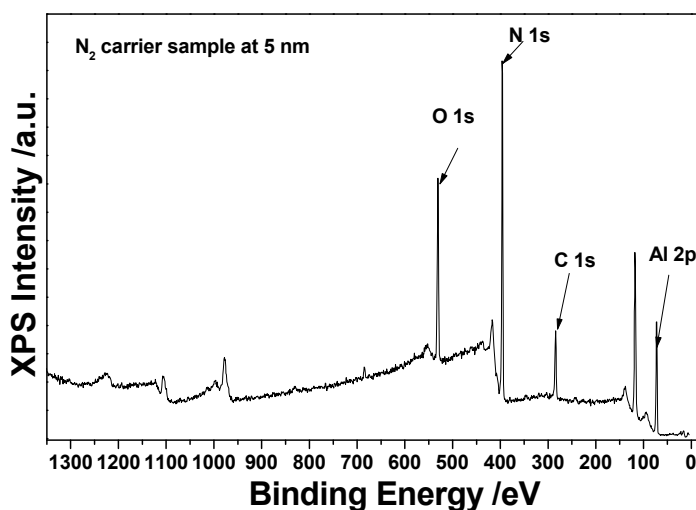


Figure S1. XPS survey scan for AlN sample grown using N<sub>2</sub> carrier gas at 5nm.

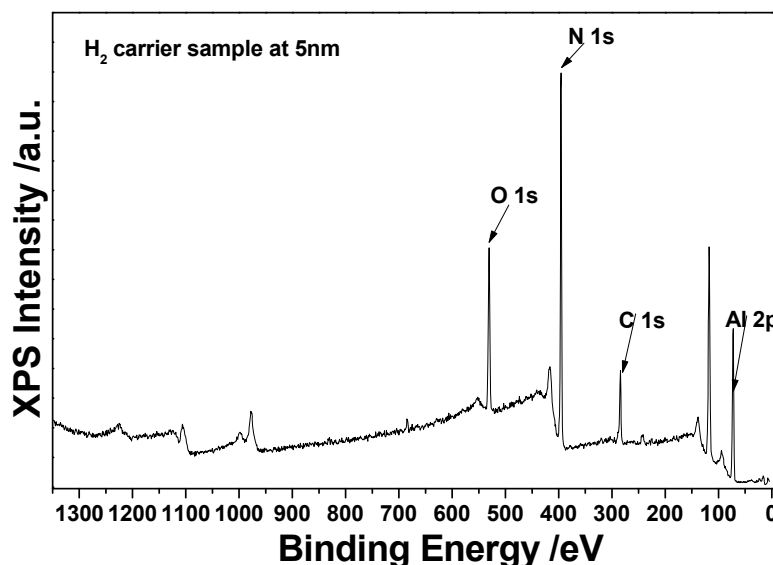


Figure S2. XPS survey scan for AlN sample grown using H<sub>2</sub> carrier gas at 5nm.

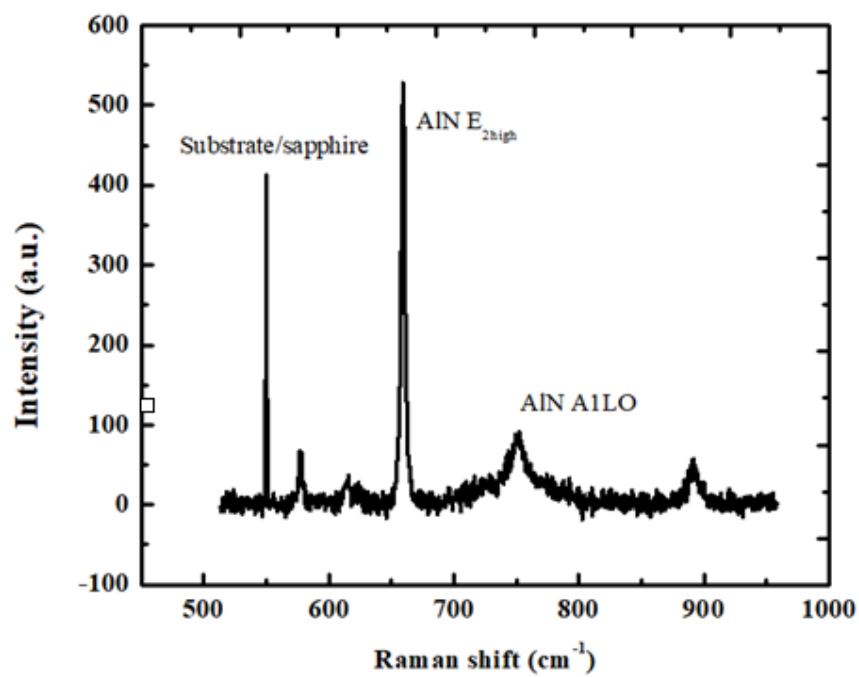


Figure S3. Full Raman spectra for AlN sample grown using N<sub>2</sub> carrier gas.

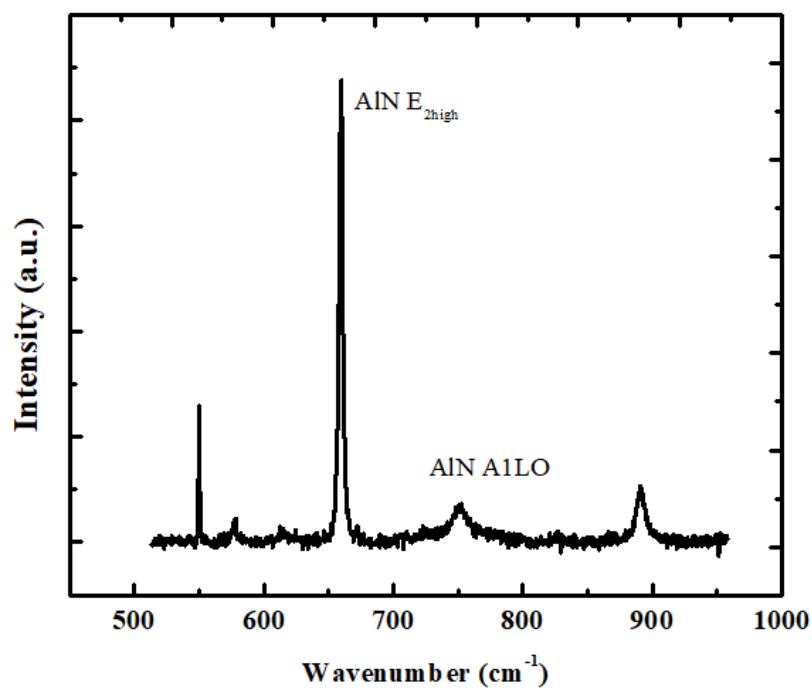


Figure S4. Full Raman spectra for AlN sample grown using H<sub>2</sub> carrier gas.